

3-Phase Bridge Rectifier + IGBT braking chopper

SKD146-L140T4

Data

Features

- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- IGBT Trench4 inside; max T_i=175°C
- CAL4F diode inside, max Tj=175°C
- I_{CM}/I_{FM} = 3xI_{c,nom}/I_{F,nom}
 Rectifier diode, max Tj=150°C

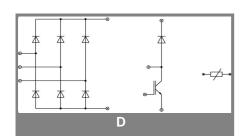
Typical Applications*

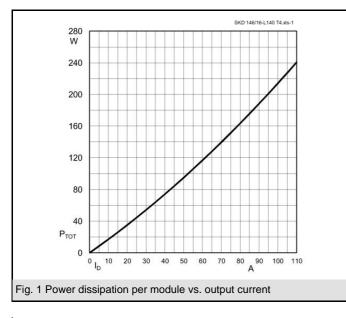
- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger

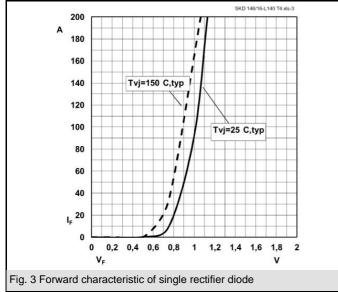
V _{RSM}	V _{RRM} , V _{DRM}	I _D = 120 A (maximum value for continuous operation)
V	V	(T _s = 70 °C)
1300	1200	SKD146/12-L140T4
1700	1600	SKD146/16-L140T4

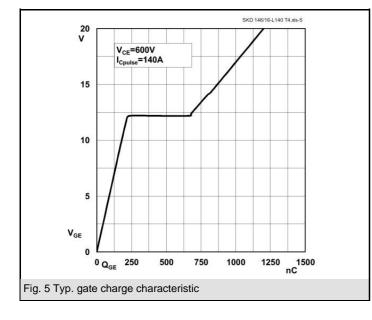
Absolute	Maximum Ratings	T _s = 25 °C, unless otherwise s	T _s = 25 °C, unless otherwise specified			
Symbol	Conditions	Values	Units			
Bridge - I	Rectifier					
I _D	T _s = °C; inductive load	140	А			
I_{FSM}/I_{TSM}	t _p = ms; ;T _{jmax}	1250	А			
i²t	t _p = ms; ;T _{jmax}	7800	A²s			
IGBT - Chopper						
V _{CES} /V _{GES}		1200 / 20	V			
I _C	T _s = °C	150 (120)	А			
I _{CM}	t _p = ms; T _s = °C	420	А			
Freewheeling - CAL Diode						
V _{RRM}		1200	V			
I _F	T _s = °C	130 (105)	А			
I _{FM}	t _p = ms; T _s = °C	450	А			
T _{vi}	Diode & IGBT (Thyristor)	- 40 + 175 (0 + 125)	°C			
T _{stg}		- 40 + 125	°C			
T _{solder}	terminals, s	260	°C			
V _{isol}	a.c. Hz, RMS min. / s	3000 / 3600	V			

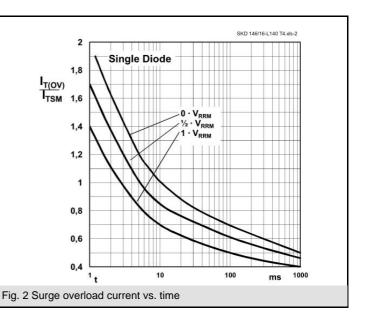
Characteristics		T _s = 25 °C	T_s = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units	
Diode - F	Rectifier					
V _{TO} / r _t	T _j = °C		0,8 / 4		V / mΩ	
R _{th(j-s)}	per diode			0,8	K/W	
IGBT - C	hopper					
V _{CE(sat)}	$I_{C} = A, T_{j} = ^{\circ}C;$ $V_{GE} = V$		1,85	2,1	V	
R _{th(j-s)}	per IGBT		0,38		K/W	
t _{d(on)} / t _r	valid for all values:		97 / 185		ns	
t _{d(off)} / t _f	V _{CC} = 600 V; V _{GE} = 15 V; I _C = 140 A; T _j = 150 °C;		443 / 82		ns	
E_{on} + E_{off}	T _j = 150 °C; R _G = 4 Ω;		52,3		mJ	
	inductive load					
CAL - Diode - Freewheeling						
V _{T(TO)} / r _t	T _i = °C		0,9 / 7,8	1,1 / 8,6	V / mΩ	
R _{th(j-s)}	per diode		0,56		K/W	
I _{RRM}	valid for all values:		30		Α	
Q _{rr}	I _F = 140 A; V _R = - 600 V; dI _F /dt = - 1700 A/μs		9		μC	
E _{off}	V _{GE} = 0 V; T _j = 150 °C		7,92		mJ	
Temperature Sensor						
R _{TS}	T = °C;		1000 (1670)		Ω	
Mechanical data						
M _S	mounting Torque	2,55		3,45	Nm	

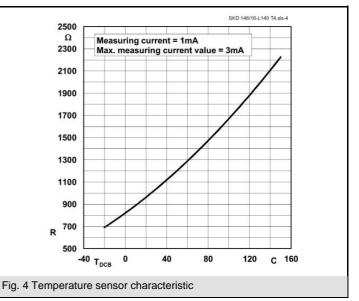


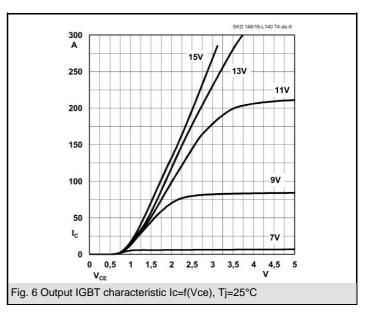


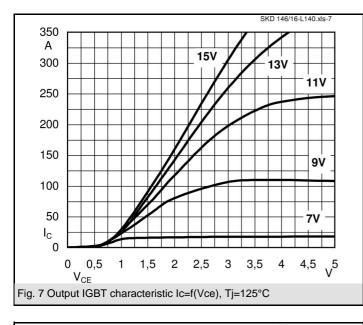


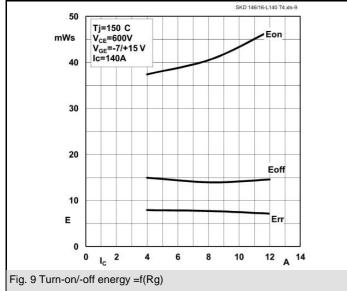


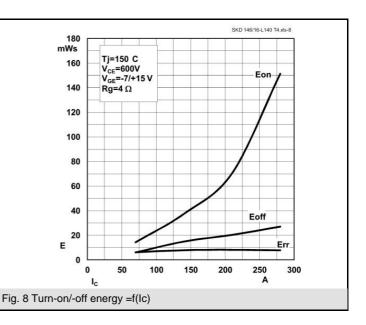


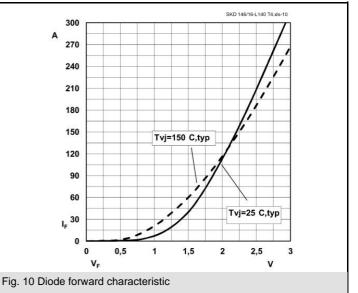


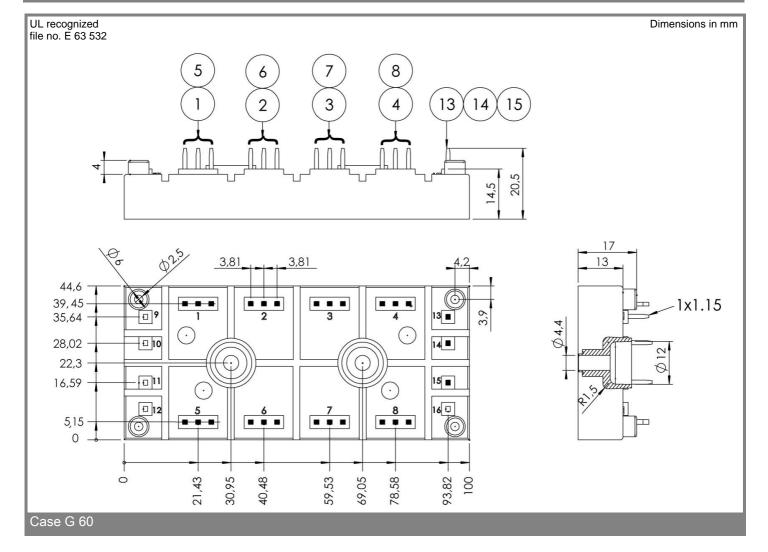


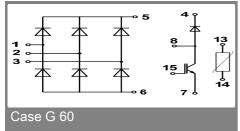












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.